## **SKiM 270GD176D**



# SKiM<sup>®</sup> 5

### **IGBT Modules**

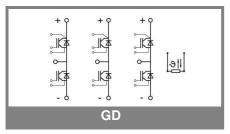
### **SKiM 270GD176D**

#### **Features**

- · Homogenous Si
- Trench = Trenchgate Technology
- · Low inductance case
- Isolated by Al<sub>2</sub>O<sub>3</sub> DCB (Direct Copper Bonded) ceramic plate
- Pressure contact technology for thermal contacts
- V<sub>CEsat</sub> with positive temperature coefficient
- High short circuit capability, self limiting to 6x I<sub>C</sub>
- Vf value is specified on chip level
- Integrated temperature sensor
- Spring contact system to attach driver PCB to the auxiliary terminals

### Typical Applications\*

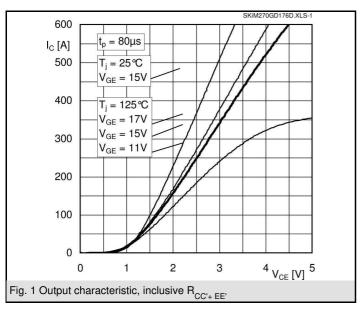
- AC inverter drives mains 575 -750 V AC
- public transport (auxiliary syst.)

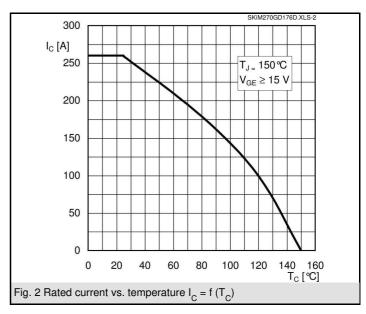


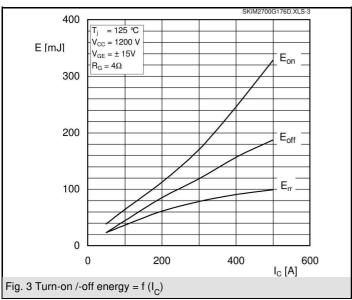
Absolute	Maximum Ratings	T <sub>c</sub> = 25 °C, unless otherwise	T <sub>c</sub> = 25 °C, unless otherwise specified					
Symbol	Conditions	Values	Units					
IGBT								
$V_{CES}$		1700	V					
I <sub>C</sub>	T <sub>s</sub> = 25 (70) °C	260 (180)	Α					
I <sub>CRM</sub>	$t_p = 1 \text{ ms}$	600	Α					
$V_{GES}$	l'	± 20	V					
$T_j (T_{stg})$		- 40 150 (125)	°C					
T <sub>cop</sub>	max. case operating temperature	125	°C					
V <sub>isol</sub>	AC, 1 min.	3300	V					
Inverse diode								
I <sub>F</sub>	T <sub>s</sub> = 25 (70) °C	215 (155)	Α					
I <sub>FRM</sub>	$t_p = 1 \text{ ms}$	540	Α					
I <sub>FSM</sub>	$t_p = 10 \text{ ms; sin.; } T_j = 150 ^{\circ}\text{C}$	2200	Α					

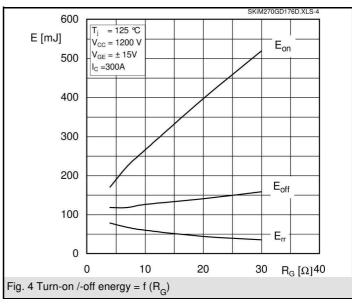
	T	- 25 °C	unlaga at	honvioo on	asified
Characte		c = 25 °C, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}$ ; $I_C = 12 \text{ mA}$	5,15	5,8	6,45	V
I <sub>CES</sub>	$V_{GE} = 0; V_{CE} = V_{CES};$ $T_i = 25 °C$			3	mA
$V_{CEO}$	T <sub>j</sub> = 25 (125) °C		1 (0,9)	1,2 (1,1)	V
r <sub>CE</sub>	T <sub>j</sub> = 25 (125) °C		3,3 (5)	4,2 (6)	mΩ
$V_{CEsat}$	$I_{Cnom} = 300 \text{ A}; V_{GE} = 15 \text{ V},$		2 (2,4)	2,45 (2,9)	V
	T <sub>j</sub> = 25 (125) °C on chip level				
C <sub>ies</sub>	V <sub>GE</sub> = 0; V <sub>CE</sub> = 25 V; f = 1 MHz		21,3		nF
C <sub>oes</sub>	$V_{GE} = 0$ ; $V_{CE} = 25 \text{ V}$ ; $f = 1 \text{ MHz}$		1,1		nF
C <sub>res</sub>	V <sub>GE</sub> = 0; V <sub>CE</sub> = 25 V; f = 1 MHz		0,9		nF
L <sub>CE</sub>				20	nH
R <sub>CC'+EE'</sub>	resistance, terminal-chip T <sub>c</sub> = 25 (125) °C		0,9 (1,1)		mΩ
$t_{d(on)}$	V <sub>CC</sub> = 1200 V				ns
t <sub>r</sub>	I <sub>Cnom</sub> = 300 A				ns
t <sub>d(off)</sub>	$R_{Gon} = R_{Goff} = 4 \Omega$				ns
t <sub>f</sub>	T <sub>j</sub> = 125 °C		.=0 (.00)		ns
E <sub>on</sub> (E <sub>off</sub> )	V <sub>GE</sub> ± 15 V		170 (120)		mJ
$E_{on} \left( E_{off} \right)$	with SKHI 65; T <sub>j</sub> = 125 °C				mJ
	V <sub>CC</sub> = 1200 V; I <sub>C</sub> = 300 A				
Inverse o	liode				
$V_F = V_{EC}$	I <sub>Fnom</sub> = 225 A; V <sub>GE</sub> = 0 V; T <sub>i</sub> = 25 (125) °C		1,7 (1,8)	1,9 (2)	V
$V_{TO}$	T <sub>j</sub> = 25 (125) °C		1,2 (0,9)	1,4 (1,1)	V
$r_T$	T <sub>j</sub> = 25 (125) °C		2,2 (4)	2,2 (4)	mΩ
I <sub>RRM</sub>	I <sub>F</sub> = 225 A; T <sub>j</sub> = 125 °C				Α
$Q_{rr}$	V <sub>GE</sub> = 1200 V di/dt = A/μs				μC
E <sub>rr</sub>	$R_{Gon} = R_{Goff} = 4 \Omega$				mJ
Thermal	characteristics				
$R_{th(j-s)}$	per IGBT			0,175	K/W
$R_{th(j-s)}$	per FWD			0,29	K/W
	ture Sensor				
R <sub>TS</sub>	T = 25 (100) °C		1 (1,67)		kΩ
tolerance	T = 25 (100) °C		3 (2)		%
Mechanic	cal data				ı
M <sub>1</sub>	to heatsink (M5)	2		3	Nm
M <sub>2</sub>	for terminals (M6)	4		5	Nm
w				460	g

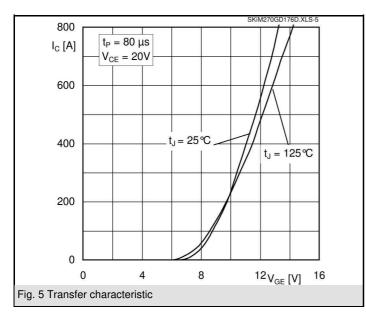
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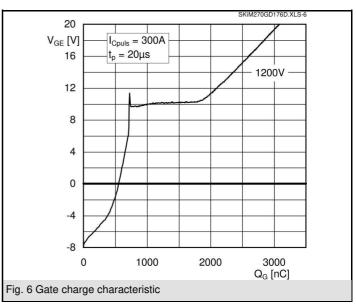




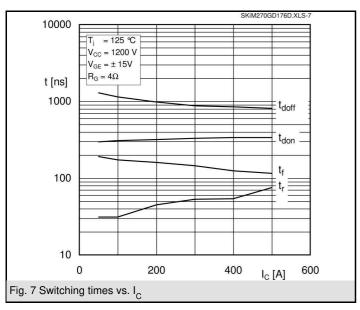


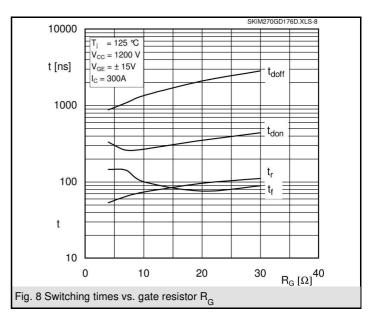


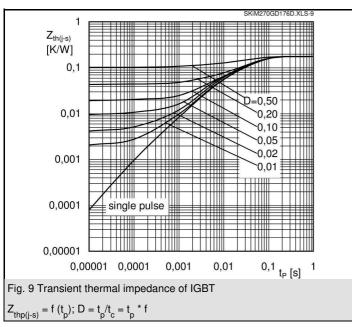


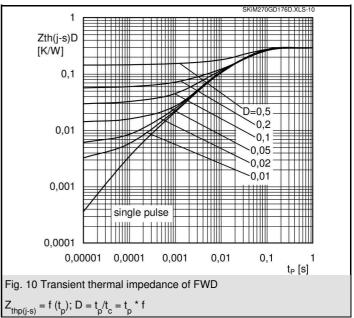


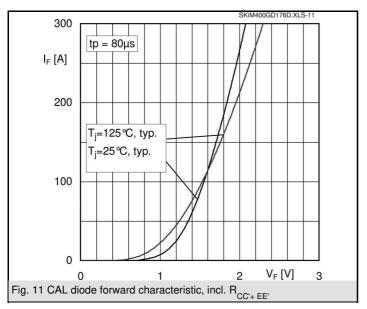
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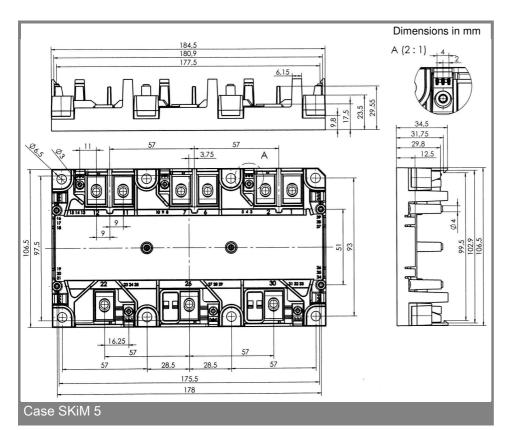


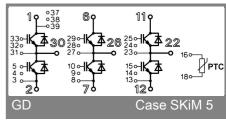






### **SKIM 270GD176D**





This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

#### \*IMPORTANT INFORMATION AND WARNINGS

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